

ABSTRACT OF THE DISCLOSURE

A semiconductor device manufacture method has the steps of: (a) forming a gate electrode traversing a corresponding one of active regions and forming extension regions of source/drain in the active region on both sides of the 5 gate electrode; (b) depositing first and second insulating films having different etching characteristics and anisotropically etching the first and second insulating films to form a side wall spacer on the side walls of the gate electrode; (c) selectively etching the first insulating film to form a retraction portion; (d) implanting ions to form source/drain regions in the silicon substrate; and (e) 10 depositing metal capable of silicidation, and performing a silicidation reaction and form silicide regions also under the retraction portion.